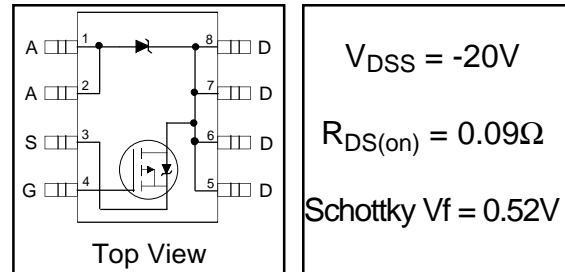


IRF7422D2

FETKY™ MOSFET & Schottky Diode

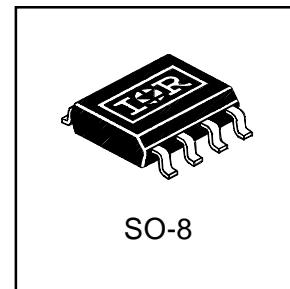
- Co-packaged HEXFET® Power MOSFET and Schottky Diode
- Ideal For Buck Regulator Applications
- P-Channel HEXFET
- Low V_F Schottky Rectifier
- Generation 5 Technology
- SO-8 Footprint



Description

The FETKY™ family of Co-packaged HEXFETs and Schottky diodes offer the designer an innovative board space saving solution for switching regulator and power management applications. Generation 5 HEXFETs utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. Combining this technology with International Rectifier's low forward drop Schottky rectifiers results in an extremely efficient device suitable for use in a wide variety of portable electronics applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics. The SO-8 package is designed for vapor phase, infrared or wave soldering techniques.



Absolute Maximum Ratings

| Parameter | Maximum | Units |
|--------------------------|-------------|-------|
| $I_D @ T_A = 25^\circ C$ | -4.3 | A |
| $I_D @ T_A = 70^\circ C$ | -3.4 | |
| I_{DM} | -33 | |
| $P_D @ T_A = 25^\circ C$ | 2.0 | W |
| $P_D @ T_A = 70^\circ C$ | 1.3 | |
| | 16 | mW/°C |
| V_{GS} | ± 12 | V |
| dv/dt | -5.0 | V/ns |
| T_J, T_{STG} | -55 to +150 | °C |

Thermal Resistance Ratings

| Parameter | Maximum | Units |
|-----------------|---------|-------|
| $R_{\theta JA}$ | 62.5 | °C/W |

Notes:

- ① Repetitive rating – pulse width limited by max. junction temperature (see fig. 11)
- ② $I_{SD} \leq -2.2A$, $di/dt \leq -50A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ C$
- ③ Pulse width $\leq 300\mu s$ – duty cycle $\leq 2\%$
- ④ Surface mounted on FR-4 board, $t \leq 10sec$.

www.irf.com

MOSFET Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------------------|--------------------------------------|-------|-------|------|-------|--|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | -20 | — | — | V | V _{GS} = 0V, I _D = -250μA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 0.07 | 0.09 | Ω | V _{GS} = -4.5V, I _D = -2.2A ③ |
| | | — | 0.115 | 0.14 | | V _{GS} = -2.7V, I _D = -1.8A ③ |
| V _{GS(th)} | Gate Threshold Voltage | -0.70 | — | — | V | V _{DS} = V _{GS} , I _D = -250μA |
| g _{fs} | Forward Transconductance | 4.0 | — | — | S | V _{DS} = -16V, I _D = -2.2A |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | -1.0 | μA | V _{DS} = -16V, V _{GS} = 0V |
| | | — | — | -25 | | V _{DS} = -16V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | -100 | nA | V _{GS} = -12V |
| | Gate-to-Source Reverse Leakage | — | — | 100 | | V _{GS} = 12V |
| Q _g | Total Gate Charge | — | 15 | 22 | nC | I _D = -2.2A |
| Q _{gs} | Gate-to-Source Charge | — | 2.2 | 3.3 | | V _{DS} = -16V |
| Q _{gd} | Gate-to-Drain ("Miller") Charge | — | 6.0 | 9.0 | | V _{GS} = -4.5V, See Fig. 6 and 9 ③ |
| t _{d(on)} | Turn-On Delay Time | — | 8.4 | — | ns | V _{DD} = -10V |
| t _r | Rise Time | — | 26 | — | | I _D = -2.2A |
| t _{d(off)} | Turn-Off Delay Time | — | 51 | — | | R _G = 6.0Ω |
| t _f | Fall Time | — | 33 | — | | R _D = 4.5Ω, See Fig. 10 ③ |
| C _{iss} | Input Capacitance | — | 610 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 310 | — | | V _{DS} = -15V |
| C _{rss} | Reverse Transfer Capacitance | — | 170 | — | | f = 1.0MHz, See Fig. 5 |

MOSFET Source-Drain Ratings and Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|---------------------------------------|------|------|------|-------|---|
| I _S | Continuous Source Current(Body Diode) | — | — | -2.5 | A | |
| I _{SM} | Pulsed Source Current (Body Diode) | — | — | -17 | | |
| V _{SD} | Body Diode Forward Voltage | — | — | -1.0 | V | T _J = 25°C, I _S = -1.8A, V _{GS} = 0V |
| t _{rr} | Reverse Recovery Time (Body Diode) | — | 56 | 84 | ns | T _J = 25°C, I _F = -2.2A |
| Q _{rr} | Reverse Recovery Charge | — | 71 | 110 | nC | di/dt = -100A/μs ③ |

Schottky Diode Maximum Ratings

| | Parameter | Max. | Units | Conditions |
|--------------------|--|------|-------|--|
| I _{f(av)} | Max. Average Forward Current | 2.8 | A | 50% Duty Cycle. Rectangular Wave, T _c = 25°C |
| | | 1.8 | | 50% Duty Cycle. Rectangular Wave, T _c = 70°C |
| I _{SM} | Max. peak one cycle Non-repetitive Surge current | 200 | A | 5μs sine or 3μs Rect. pulse |
| | | 20 | | 10ms sine or 6ms Rect. pulse |
| | | | | Following any rated load condition & with V _{rrm} applied |

Schottky Diode Electrical Specifications

| | Parameter | Max. | Units | Conditions |
|-----------------|------------------------------|------|-------|---|
| V _{fm} | Max. Forward voltage drop | 0.57 | V | I _f = 3.0, T _J = 25°C |
| | | 0.77 | | I _f = 6.0, T _J = 25°C |
| | | 0.52 | | I _f = 3.0, T _J = 125°C |
| | | 0.79 | | I _f = 6.0, T _J = 125°C |
| I _{rm} | Max. Reverse Leakage current | 0.13 | mA | T _J = 25°C |
| | | 18 | | T _J = 125°C |
| C _t | Max. Junction Capacitance | 310 | pF | V _r = 5Vdc (100kHz to 1 MHz) 25°C |
| dv/dt | Max. Voltage Rate of Charge | 4900 | V/μs | Rated V _r |

(HEXFET is the reg. TM for International Rectifier Power MOSFET's)

Power Mosfet Characteristics

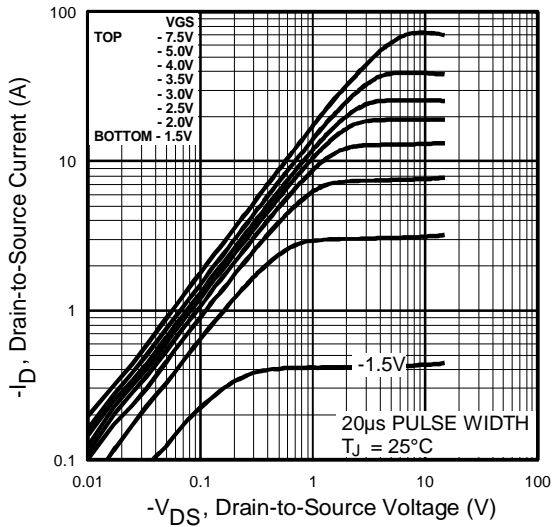


Fig 1. Typical Output Characteristics

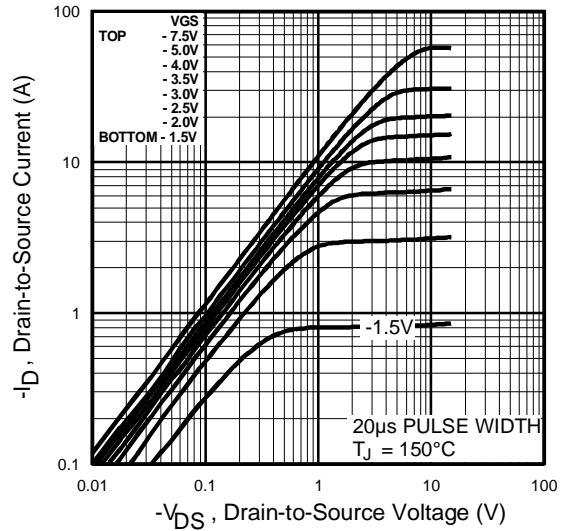


Fig 2. Typical Output Characteristics

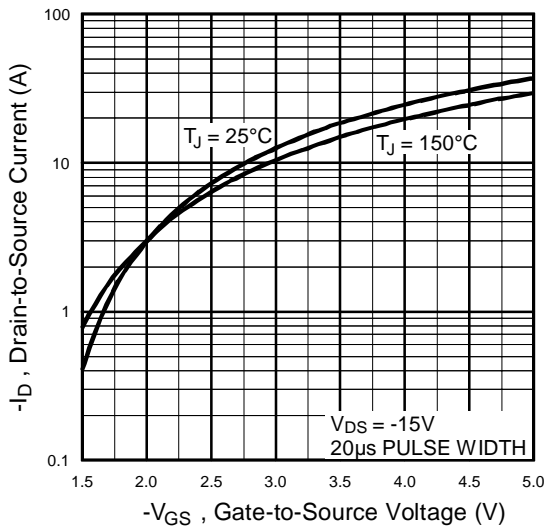


Fig 3. Typical Transfer Characteristics

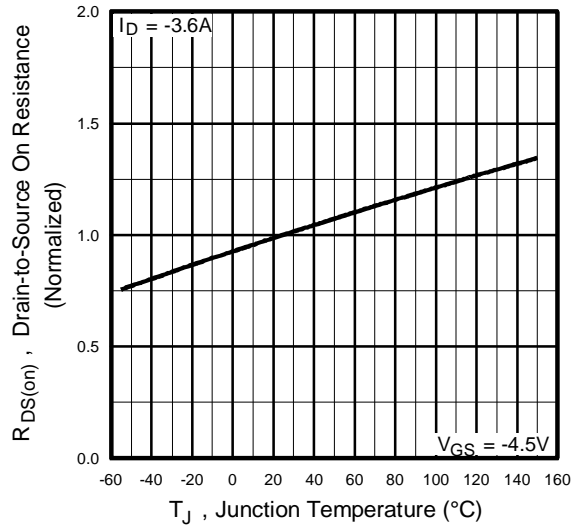


Fig 4. Normalized On-Resistance Vs. Temperature

Power Mosfet Characteristics

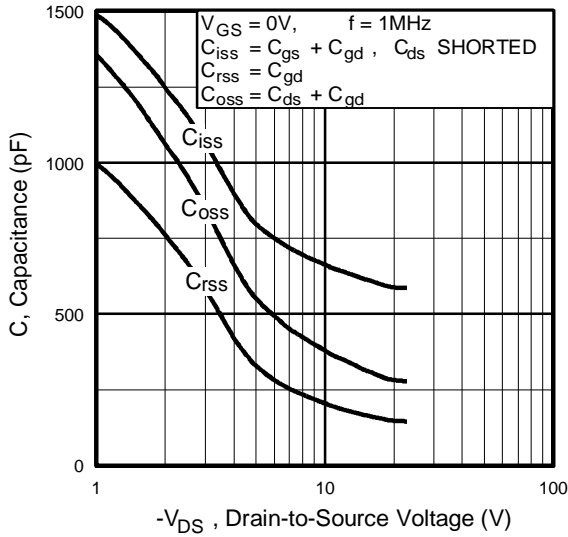


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

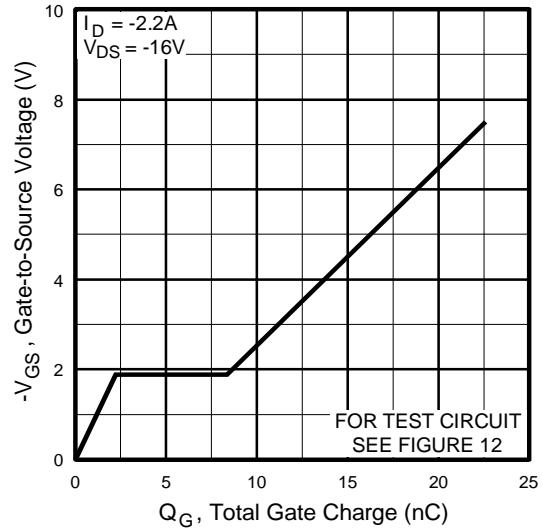


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

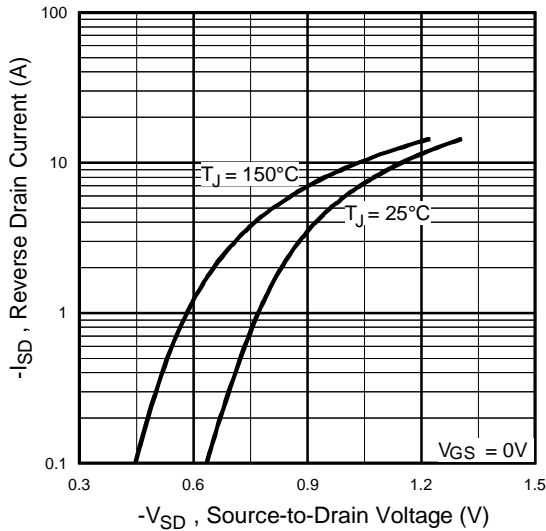


Fig 7. Typical Source-Drain Diode Forward Voltage

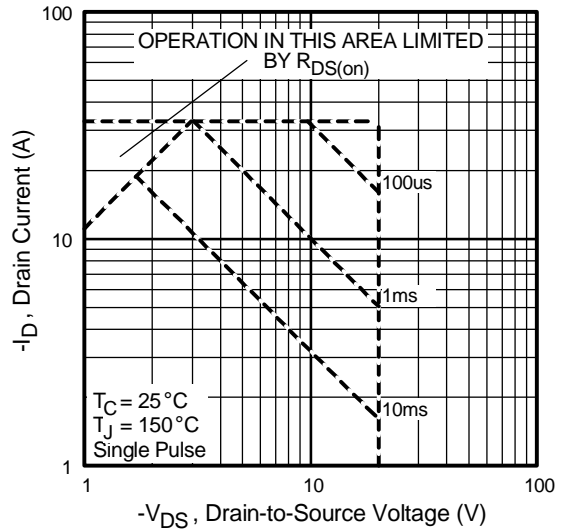


Fig 8. Maximum Safe Operating Area

Power Mosfet Characteristics

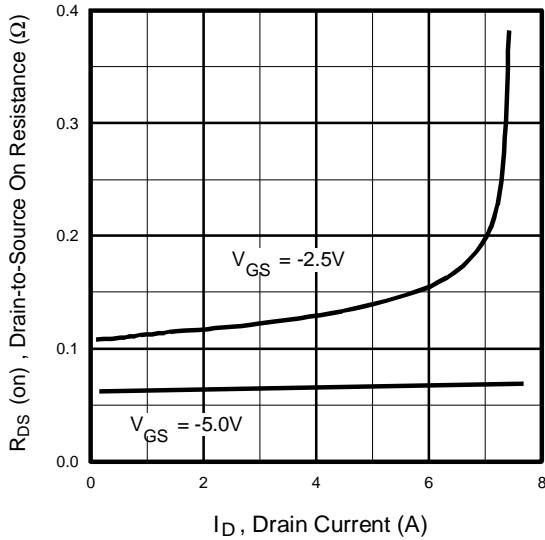
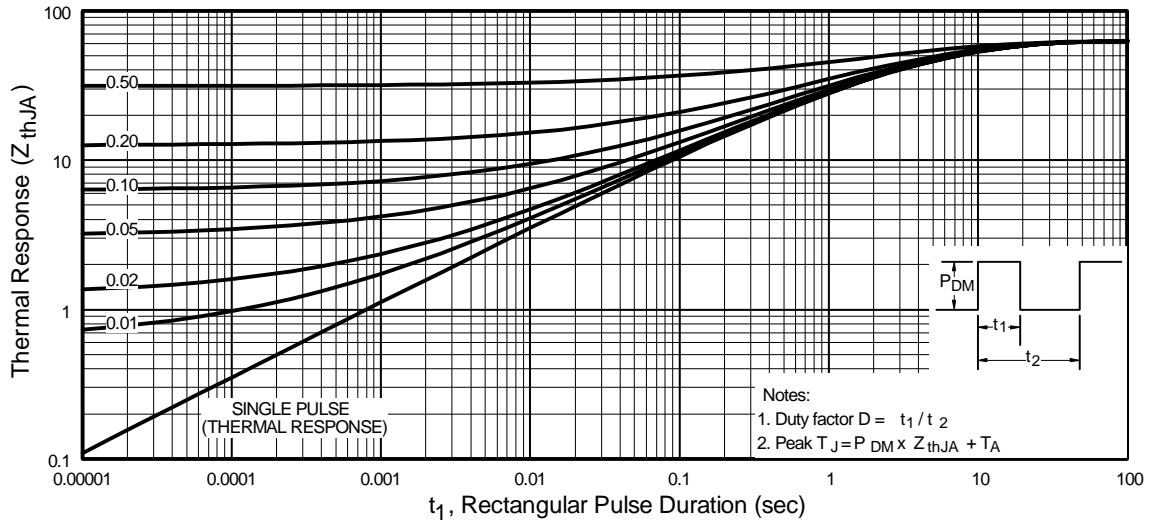


Fig 10. Typical On-Resistance Vs. Drain Current

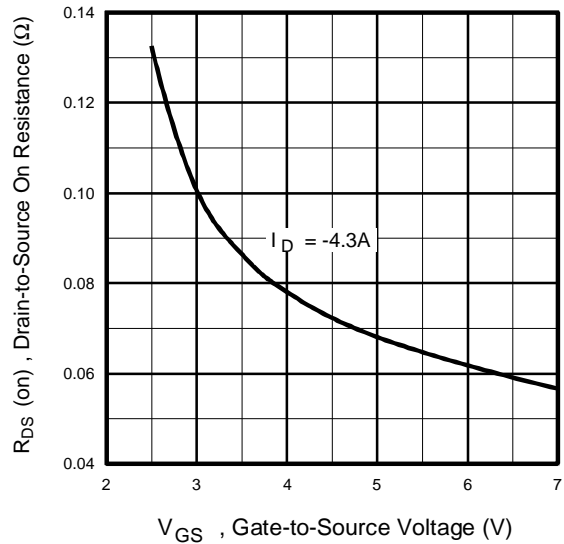


Fig 11. Typical On-Resistance Vs. Gate Voltage

Schottky Diode Characteristics

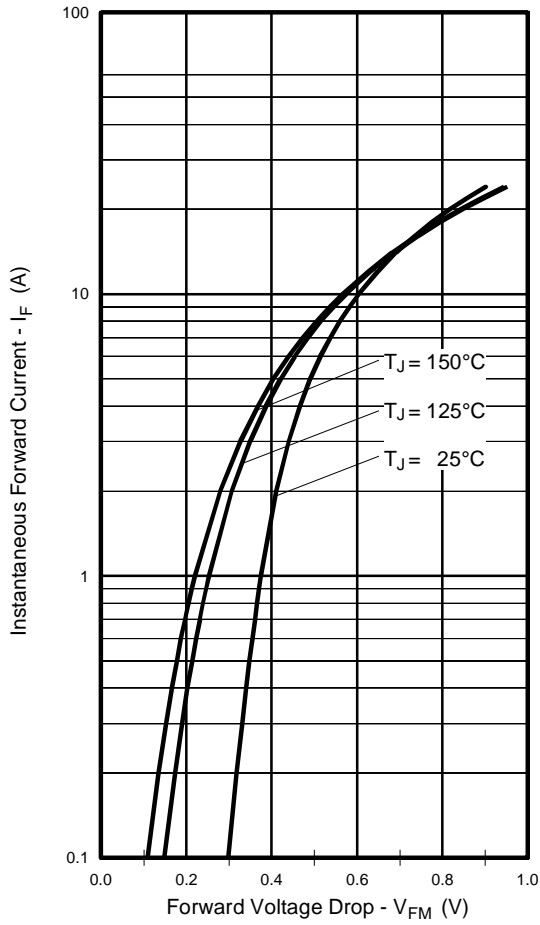


Fig. 12 - Typical Forward Voltage Drop Characteristics

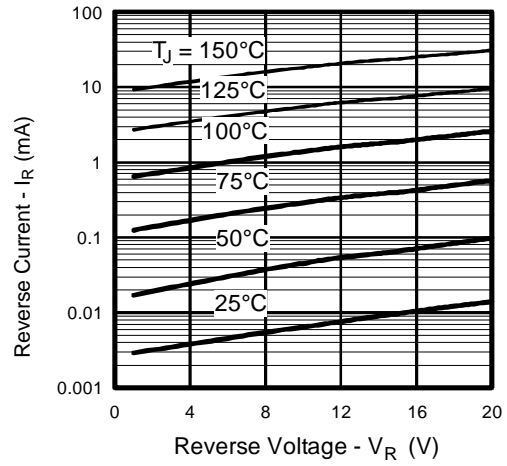


Fig. 13 - Typical Values of Reverse Current Vs. Reverse Voltage

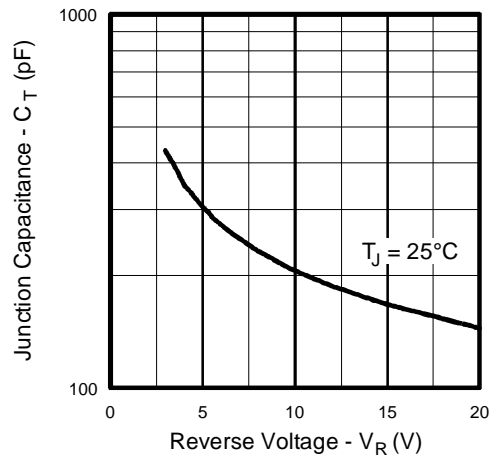
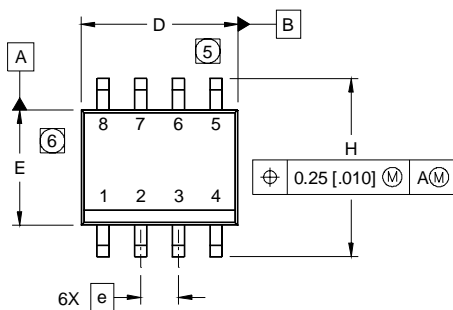
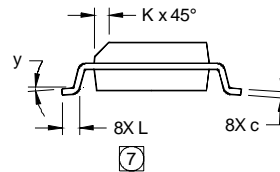
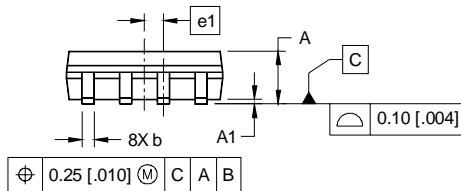


Fig. 14 - Typical Junction Capacitance Vs. Reverse Voltage

SO-8 Package Details



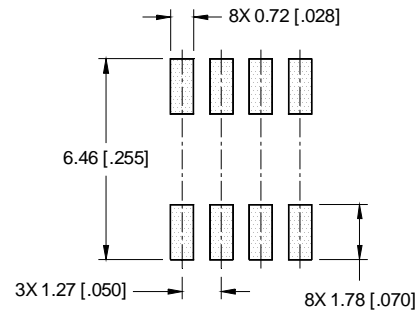
| DIM | INCHES | | MILLIMETERS | |
|-----|------------|-------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | .0532 | .0688 | 1.35 | 1.75 |
| A1 | .0040 | .0098 | 0.10 | 0.25 |
| b | .013 | .020 | 0.33 | 0.51 |
| c | .0075 | .0098 | 0.19 | 0.25 |
| D | .189 | .1968 | 4.80 | 5.00 |
| E | .1497 | .1574 | 3.80 | 4.00 |
| e | .050 BASIC | | 1.27 BASIC | |
| e1 | .025 BASIC | | 0.635 BASIC | |
| H | .2284 | .2440 | 5.80 | 6.20 |
| K | .0099 | .0196 | 0.25 | 0.50 |
| L | .016 | .050 | 0.40 | 1.27 |
| y | 0° | 8° | 0° | 8° |



NOTES:

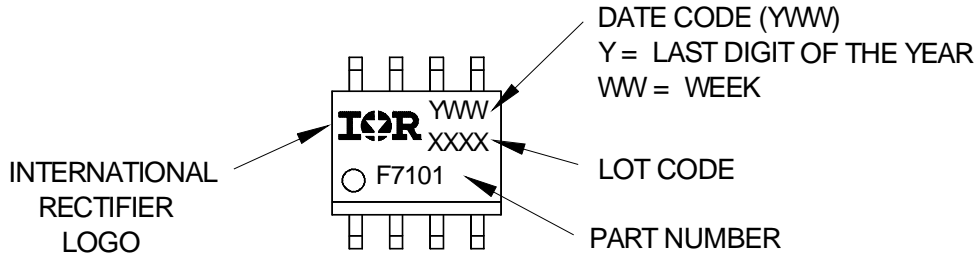
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking

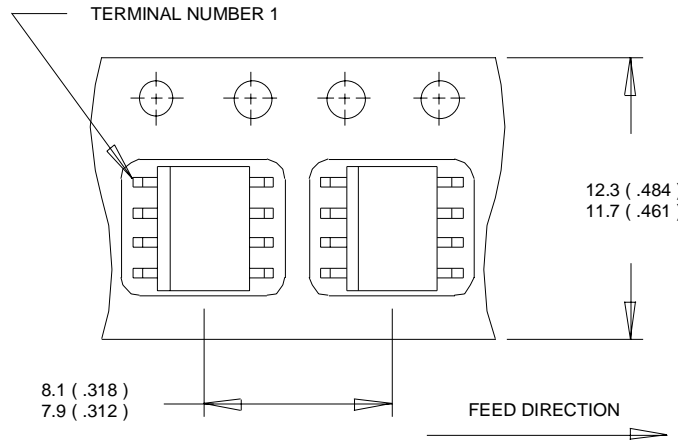
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



IRF7422D2

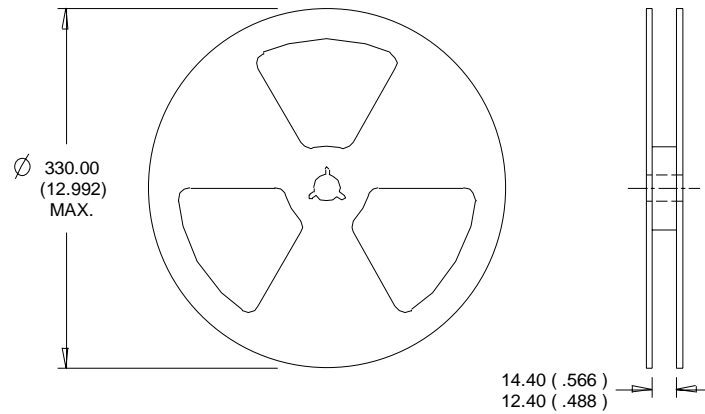
International
IR Rectifier

Tape and Reel



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 11/01

www.irf.com